

SEMICONDUCTOR DEVICE AND FABRI- CATION PROCESS THEREFOR

Abstract

A semiconductor device, and a method of fabricating the device, having a copper wiring level and an aluminum bond pad above the copper wiring level. In addition to a barrier layer which is normally present to protect the copper wiring level, there is a composite layer between the aluminum bond pad and the barrier layer to make the aluminum bond pad more robust so as to withstand the forces of bonding and probing. The composite layer is a sandwich of a refractory metal and a refractory metal nitride.